Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-11. (Cancelled)
- 12. (Currently amended) A method for manufacturing a test sensor, comprising:

forming a multiple layer device, including depositing a <u>first</u> metallic layer onto a substrate material by physical vapor deposition; <u>depositing an intermediate, sacrificial</u> <u>layer on said metallic layer</u>; and depositing an electrically non-conductive layer adjacent said <u>metallic intermediate</u>, <u>sacrificial</u> layer by plasma enhanced chemical vapor deposition; and

applying an amount of laser energy to said multiple layer device to selectively remove a portion of said intermediate, sacrificial layer, thereby causing and a corresponding portion of either said metallic layer or said non-conductive layer to be removed.

- 13. (Cancelled)
- 14. (Currently amended) The method of claim 13 12, wherein said amount of laser energy is in the range of approximately 40 mJ/cm² to 450 mJ/cm².
- 15. (Currently amended) The method of claim 13 12, wherein said laser energy is provided by includes an ion-beam.
- 16. (Currently amended) The method of claim 13 12, wherein said laser energy is provided by includes an electron beam.

- 17. (Currently amended) The method of claim 13 12, wherein the metallic layer includes at least one of copper, silver, gold, platinum, palladium, nickel, or aluminum.
- 18. (Currently amended) The method of claim $\frac{13}{12}$, wherein the electrically non-conductive layer has a thickness less than or substantially equal to 1 μ m.
- 19. (Currently amended) The method of claim 13 12, wherein the intermediate, sacrificial layer is made of polytetrafluorethylene.
- 20. (Currently amended) The method of claim 19, wherein the intermediate, sacrificial layer is deposited onto said metallic layer by plasma enhanced chemical vapor deposition.
- 21. (Currently amended) The method of claim 13 12, wherein the substrate is made of a polymer material.
- 22. (Previously presented) The method of claim 21, wherein the substrate is flexible.
- 23. (Currently amended) The method of claim 13 12, further comprising: depositing at least one of a second metallic layer, a second intermediate, sacrificial layer, or a second non-metallic conductive layer on said multiple layer device.
 - 24. (Currently amended) The method of claim 13 12, further comprising: removing said corresponding portion of said non-conductive layer.
- 25. (Currently amended) The method of claim 13 12, further comprising: performing plasma activation before depositing said metallic layer, said nonconductive layer, or said intermediate layer.

- 26. (New) The method of claim 12, wherein said energy is provided by a laser.
- 27. (New) The method of claim 12, wherein the intermediate, sacrificial layer is made of a Teflon-like compound.
- 28. (New) The method of claim 12, wherein the electrically non-conductive layer is made of a ceramic layer comprising MgO.
- 29. (New) The method of claim 12, wherein the electrically non-conductive layer is not suitable for laser ablation.